



AMENDMENT TRANSMITTAL LETTER

Docket No.
M4065.0210/P210

Application No.
09/588,008

Filing Date
June 6, 2000

Examiner
Hoa B. Trinh

Art Unit
2814

Applicant(s): Yang, et al.

Invention: IMPROVED MEMORY CELL CAPACITOR STRUCTURE AND METHOD OF FORMATION

TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED

	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	33	- 20 =	13	x 18.00	234.00
Independent Claims	3	- 3 =	0	x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					

☒ Large Entity

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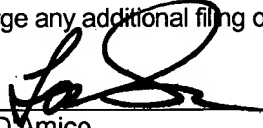
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Dated: September 4, 2002


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Docket No.: M4065.0210/P210
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Yang et al.

Application No.: 09/588,008

Group Art Unit: 2814

Filed: June 6, 2000

Examiner: Vikki H. Trinh

For: IMPROVED MEMORY CELL CAPACITOR
STRUCTURE AND METHOD OF
FORMATION

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AMENDMENT UNDER 37 CFR §1.116

ATTN: BOX AF
Commissioner for Patents
Washington, DC 20231

Dear Sir:

This paper is in response to the Office Action dated June 4, 2002 finally rejecting claims 1-31, 97, and 98, please amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please replace claims 1, 97, and 98 with amended claims 1, 97, and 98 below.

1. (amended) A capacitor for a semiconductor device, said capacitor comprising:

a bottom conducting layer;

a dielectric layer formed over said bottom conducting layer; and

an annealed oxygen permeable top conducting layer formed over said dielectric